TOSHIBA Bi-CMOS Digital Integrated Circuit Silicon Monolithic

TB2904HQ (o)

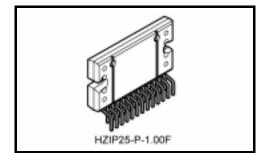
Maximum Power 43 W BTL \times 4-ch Audio Power IC

The TB2904H (o) is 4-ch BTL audio amplifier for car audio applications.

This IC can generate higher power: POUT MAX = 43 W as it includes the pure complementary P-ch and N-ch DMOS output stage.

It is designed to yield low distortion ratio for 4-ch BTL audio power amplifier, built-in standby function, muting function, and various kinds of protectors.

Additionally, Off-set detector is built in.



Weight: 7.7 g (typ.)

Features

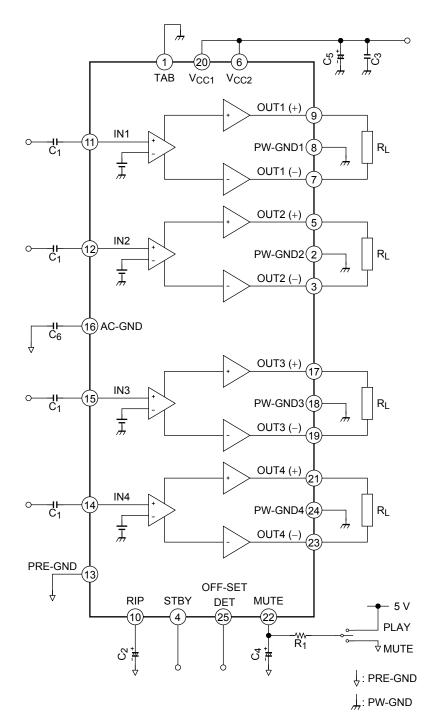
- High power output
 - : POUT MAX (1) = 43 W (typ.)
 - P (V_{CC} = 14.4 V, f = 1 kHz, JEITA max, R_L = 4 Ω)
 - : POUT MAX (2) = 39 W (typ.)
 - $(V_{CC} = 13.7 \text{ V}, \text{ f} = 1 \text{ kHz}, \text{ JEITA max}, \text{ RL} = 4 \Omega)$
 - $: P_{OUT}(1) = 26 W (typ.)$
 - $(V_{CC} = 14.4 \text{ V}, \text{ f} = 1 \text{ kHz}, \text{ THD} = 10\%, \text{ R}_{L} = 4 \Omega)$
 - $P_{OUT}(2) = 23 \text{ W (typ.)}$
 - $(V_{CC} = 13.2 \text{ V}, \text{ f} = 1 \text{ kHz}, \text{ THD} = 10\%, \text{ R}_{L} = 4 \Omega)$
- Low distortion ratio: THD = 0.015% (typ.)

$$(V_{CC} = 13.2 \text{ V}, \text{ f} = 1 \text{ kHz}, P_{OUT} = 5 \text{ W}, \text{ RL} = 4 \Omega)$$

Low noise: $V_{NO} = 90 \ \mu Vrms$ (typ.) ($V_{CC} = 13.2 \ V$, $Rg = 0 \ \Omega$, $BW = 20 \ Hz$ to 20 kHz, $R_L = 4 \ \Omega$)

- Built-in standby switch function (pin 4)
- Built-in muting function (pin 22)
- Built-in Off-set detection function (pin 25)
- Built-in various protection circuits: Thermal shut down, overvoltage, out to GND, out to VCC, out to out short, speaker burned
- Operating supply voltage: V_{CC} (opr) = 9 to 18 V (R_L = 4 Ω)
 - Note 1: Since this device's pins have a low withstanding voltage, please handle it with care.
 - Note 2: Install the product correctly. Otherwise, it may result in break down, damage and/or degradation to the product or equipment.
 - Note 3: These protection functions are intended to avoid some output short circuits or other abnormal conditions temporarily. These protect functions do not warrant to prevent the IC from being damaged. In case of the product would be operated with exceeded guaranteed operating ranges, these protection features may not operate and some output short circuits may result in the IC being damaged.

Block Diagram



Note: Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purpose.

Caution and Application Method (Description is made only on the single channel)

1. Voltage Gain Adjustment

This IC has no NF (negative feedback) Pins. Therefore, the voltage gain can not be adjusted, but it makes the device a space and total costs saver.

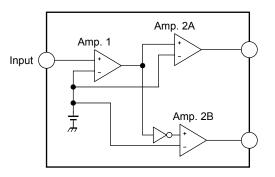


Figure 1 Block Diagram

2. Standby SW Function (pin 4)

By means of controlling pin 4 (standby pin) to High and Low, the power supply can be set to ON and OFF. The threshold voltage of pin 4 is set at about 3 V_{BE} (typ.), and the power supply current is about 2 μ A (typ.) in the standby state.

Control Voltage of Pin 4: VSB

Stand-by	Power	V _{SB} (V)
ON	OFF	0 to 1.5
OFF	ON	3.5 to 6 V

When changing the time constant of pin 4, check the pop noise.

Advantage of Standby SW

- (1) Since V_{CC} can directly be controlled to ON or OFF by the microcomputer, the switching relay can be omitted.
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching.

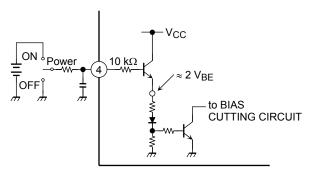


Figure 2 With pin 4 set to High, Power is turned ON

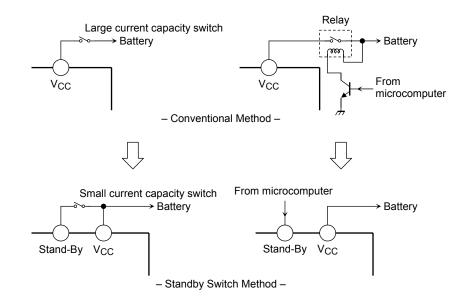


Figure 3

3. Muting Function (pin 22)

Audio muting function is enabled when pin 22 is Low. When the time constant of the muting function is determined by R_1 and C_4 it should take into account the pop noise. The pop noise, which is generated when the power or muting function is turned ON/OFF, will vary according to the time constant. (Refer to Figure 4 and Figure 5.)

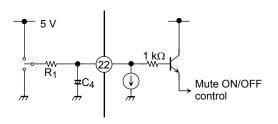
The pin 22 is designed to operate off 5 V so that the outside pull-up resistor R_1 is determined on the basic of this value:

ex) When control voltage is changed in to 6 V from 5 V. $6~{\rm V}/5~{\rm V}\times47~{\rm k}=56~{\rm k}$

Additionally, as the V_{CC} is rapidly falling, the IC internal low voltage muting operates to eliminate the large pop noise basically.

The low voltage muting circuit pull 200 μA current into the IC so that the effect of the internal low voltage muting does not become enough if the R_1 is too small value.

To obtain enough operation of the internal low voltage muting, a series resistor, R_1 at pin 22 should be 47 k Ω or more.



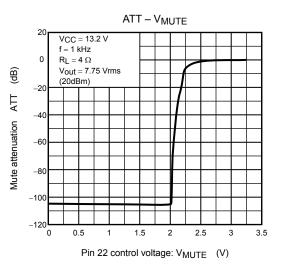
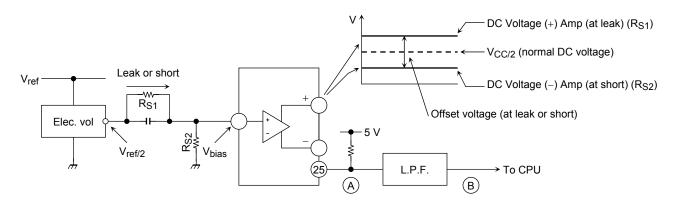


Figure 4 Muting Function

Figure 5 Mute Attenuation – V_{MUTE} (V)

4. Off-set detection function

In case of Appearing output offset voltage by Generating a Large Leakage Current on the input Capacitor etc.





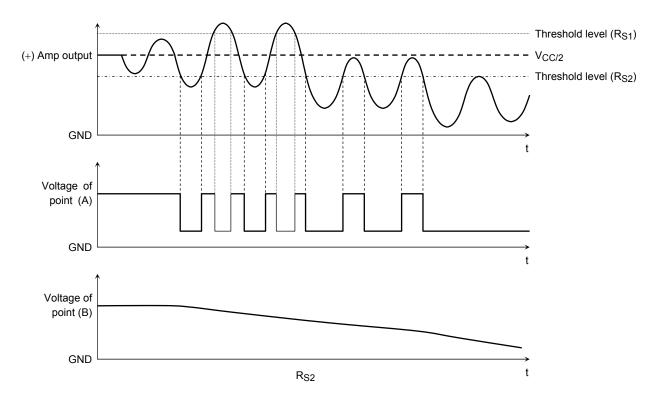


Figure 7 Wave Form

5. Prevention of speaker burning accident (in case of rare short circuit of speaker)

When the direct current resistance between OUT+ and OUT– terminal becomes 1 Ω or less and output current over 4 A flows, this IC makes a protection circuit operate and suppresses the current into a speaker. This system makes the burning accident of the speaker prevent as below mechanism.

<The guess mechanism of a burning accident of the speaker>

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Abnormal output offset voltage (voltage between OUT+ and OUT–) over 4 V is made by the external circuit failure.(Note 1)

The speaker imepedance becomes 1 Ω or less as it is in a rare short circuit condition.

The current more than 4 A flows into the speaker and the speaker is burned.

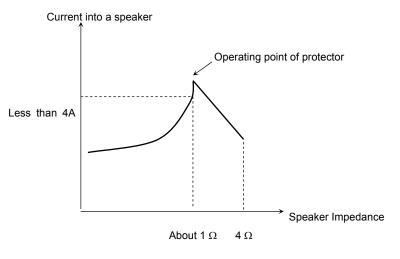


Figure 8

Note 1: It is appeared by biased input DC voltage (For example, large leakage of the input capacitor, short-circuit between copper patterns of PCB.)

6. Pop Noise Suppression

Since the AC-GND pin (pin 16) is used as the NF pin for all amps, the ratio between the input capacitance (C1) and the AC-to-GND capacitance (C6) should be 1:4.

Also, if the power is turned OFF before the C1 and C6 batteries have been completely charged, pop noise will be generated because of the DC input unbalance.

To counteract the noise, it is recommended that a longer charging time be used for C2 as well as for C1 and C6. Note that the time which audio output takes to start will be longer, since the C2 makes the muting time (the time from when the power is turned ON to when audio output starts) is fix.

The pop noise which is generated when the muting function is turned ON/OFF will vary according to the time constant of C4.

The greater the capacitance, the lower the pop noise. Note that the time from when the mute control signal is applied to C4 to when the muting function is turned ON/OFF will be longer.

Component	Recommended		Eff		
Name	Value	Purpose	Lower than recommended value	3 • • • • • • • • • • • • • • • • • • •	
C1	0.22 μF	To eliminate DC	increased Cut-off frequency is reduced g		Pop noise is generated when V_{CC} is ON
C2	10 μF	To reduce ripple	Powering ON/OFF is faster	wering ON/OFF is faster Powering ON/OFF takes longer	
C3	0.1 μF	To provide sufficient oscillation margin	Reduces noise and provides s		
C4	1 μF	To reduce pop noise	High pop noise. Duration until muting function is turned ON/OFF is shortLow pop noise. Duration until muting function is turned ON/OFF is long		
C5	3900 μF	Ripple filter	Power supply ripple filtering		
C6	1 μF	NF for all outputs	Pop noise is suppressed when	Pop noise is generated when V_{CC} is ON	

7. External Component Constants

Note: If recommended value is not used.

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Peak supply voltage (0.2 s)	V _{CC (surge)}	50	V
DC supply voltage	V _{CC (DC)}	28	V
Operation supply voltage	V _{CC (opr)}	18	V
Output current (peak)	I _{O (peak)}	9	А
Power dissipation	P _D (Note 2)	125	W
Operation temperature	T _{opr}	-40 to 85	°C
Storage temperature	T _{stg}	-55 to 150	°C

Note 2: Package thermal resistance $\theta_{j-T} = 1^{\circ}C/W$ (typ.) (Ta = 25°C, with infinite heat sink)

The absolute maximum ratings of a semiconductor device are a set of specified parameter values, which must not be exceeded during operation, even for an instant. If any of these rating would be exceeded during operation, the device electrical characteristics may be irreparably altered and the reliability and lifetime of the device can no longer be guaranteed. Moreover, these operations with exceeded ratings may cause break down, damage and/or degradation to any other equipment. Applications using the device should be designed such that each maximum rating will never be exceeded in any operating conditions. Before using, creating and/or producing designs, refer to and comply with the precautions and conditions set forth in this documents.

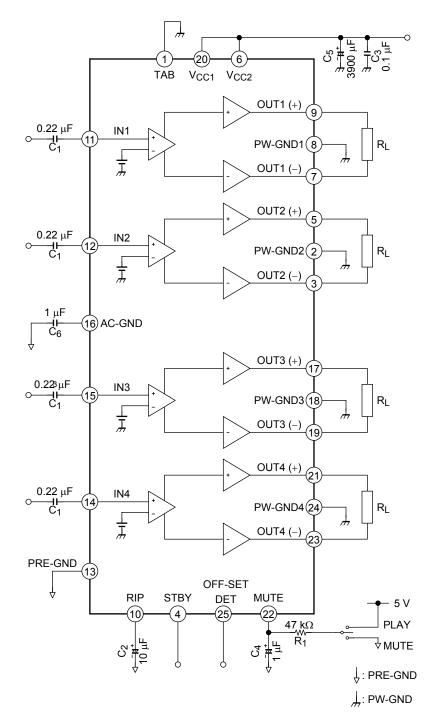
Electrical Characteristics (unless otherwise specified, $V_{CC} = 13.2 \text{ V}$, f = 1 kHz, $R_L = 4 \Omega$, Ta = 25°C)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Quiescent current	ICCQ	—	$V_{IN} = 0$	_	170	340	mA	
	P _{OUT} MAX (1)	—	V _{CC} = 14.4 V, max POWER		43		w	
Output power	P _{OUT} MAX (2)	—	V _{CC} = 13.7 V, max POWER	_	39			
Oulput power	P _{OUT} (1)	_	$V_{CC} = 14.4 \text{ V}, \text{ THD} = 10\%$		26			
	P _{OUT} (2)	_	THD = 10%	21	23			
Total harmonic distortion	THD	_	$P_{OUT} = 5 W$		0.015	0.15	%	
Voltage gain	GV	—	V _{OUT} = 0.775 Vrms	24	26	28	dB	
Voltage gain ratio	ΔG_V	_	V _{OUT} = 0.775 Vrms	-1.0	0	1.0	dB	
Output noise voltage	V _{NO} (1)	—	Rg = 0 Ω, DIN45405		100	_	μVrms	
Oulput hoise voltage	V _{NO} (2)	_	Rg = 0 Ω, BW = 20 Hz~20 kHz		90	200		
Ripple rejection ratio	R.R.	_		50	60		dB	
Cross talk	C.T.	_	$R_g = 620 \ \Omega$ V _{OUT} = 0.775 Vrms	_	70		dB	
Output offset voltage	VOFFSET	—	_	-150	0	150	mV	
Input resistance	R _{IN}	—	_	_	90	_	kΩ	
Standby current	I _{SB}	—	Standby condition	_	2	10	μA	
Standby control voltage	V _{SB} H	—	POWER: ON	3.5	_	6.0	v	
Standby control voltage	V _{SB} L	—	POWER: OFF	0	_	1.5	v	
Mute control voltage	V _M H	_	MUTE: OFF	3.0		6.0	v	
white control vollage	V _M L	_	MUTE: ON, $R_1 = 47 \text{ k}\Omega$	0		0.5	v	
Mute attenuation	ATT M	_	MUTE: ON V _{OUT} = 7.75 Vrms→Mute: OFF	85	100		dB	

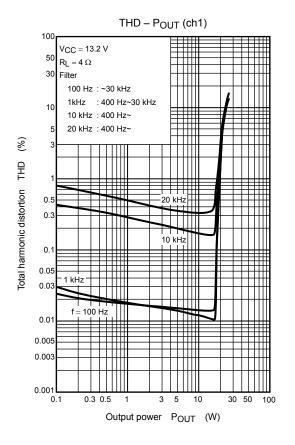
Offset detection

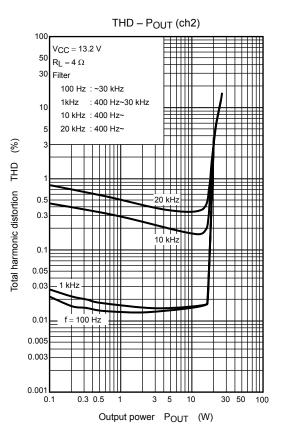
Detection threshold voltage	Voff-set		$\begin{array}{l} Rpull-up = 47 \ k\Omega, \ +V = 5.0V \\ Based \ on \ output \ DC \ voltage \end{array}$	±1.0	±1.5	±2.0	V
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Test Circuit

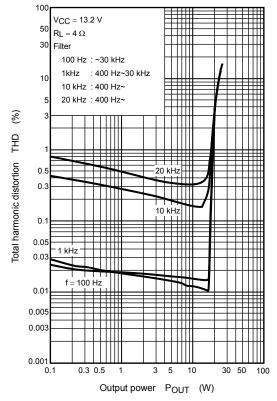


Components in the test circuits are only used to obtain and confirm the device characteristics. These components and circuits do not warrant to prevent the application equipment from malfunction or failure.

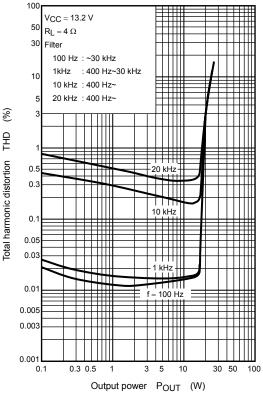




THD – P_{OUT} (ch3)



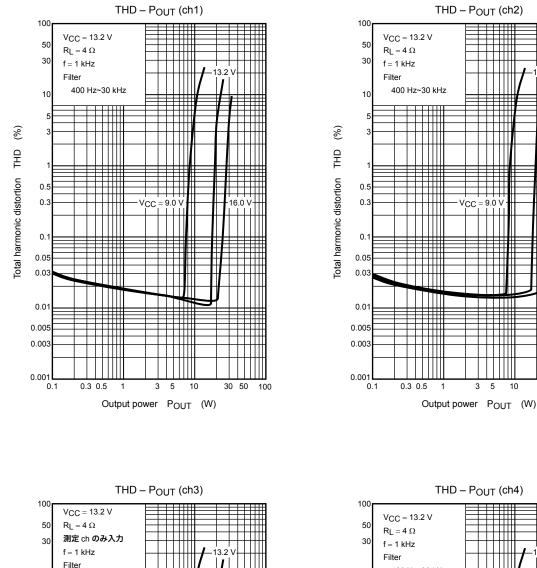
THD – P_{OUT} (ch4)

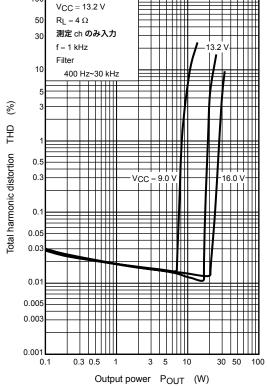


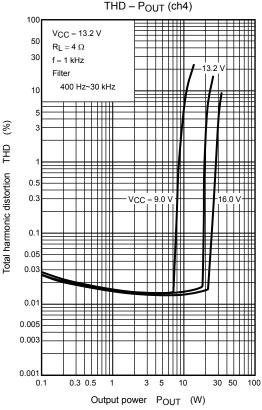
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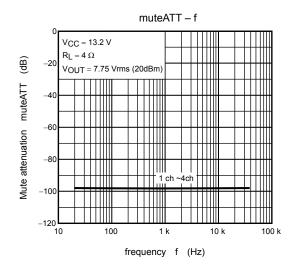
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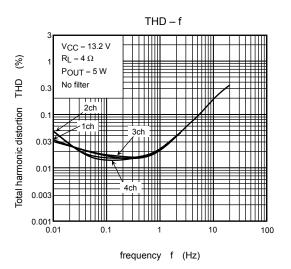
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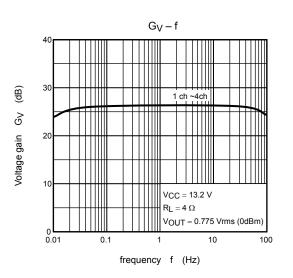


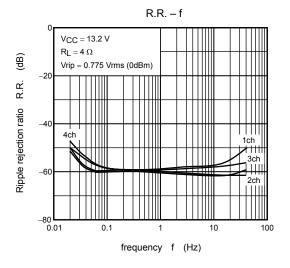


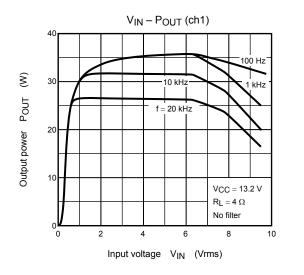


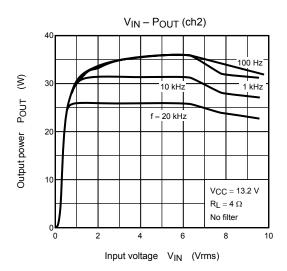


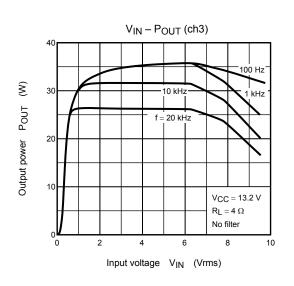


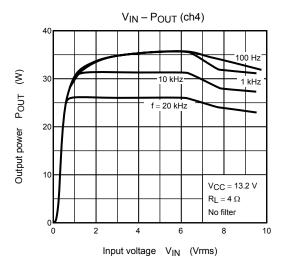


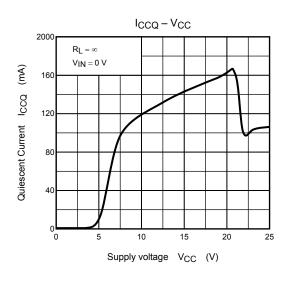




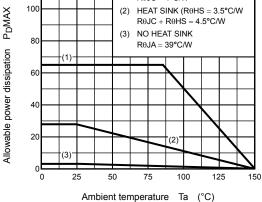








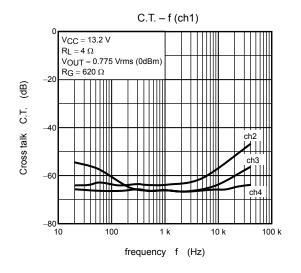
P_DMAX – Ta INFINITE HEAT SINK (1) $R\theta JC = 1^{\circ}C/W$

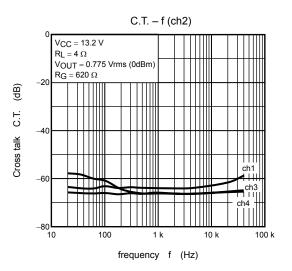


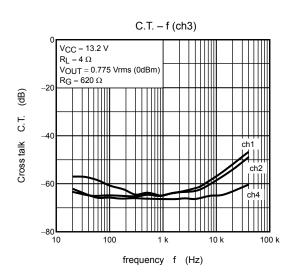
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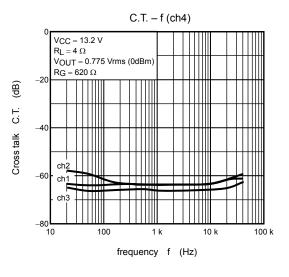
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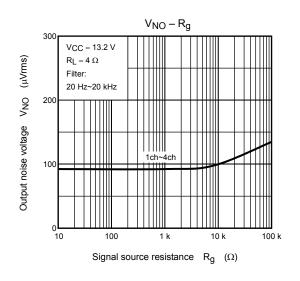
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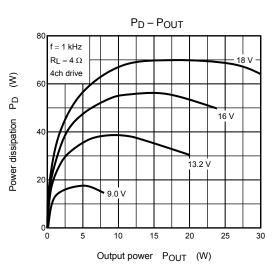








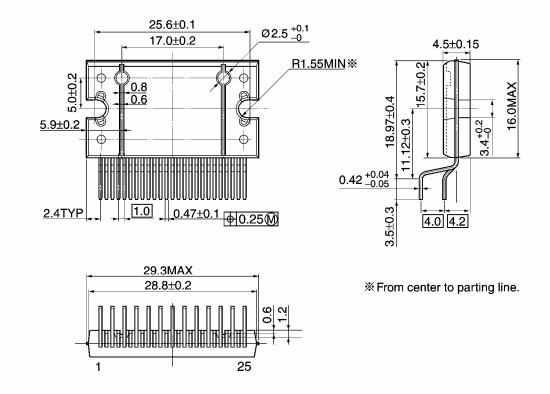




Package Dimensions

HZIP25-P-1.00F

Unit: mm



Weight: 7.7 g (typ.)

	About solderability, following conditions were confirmed					
Solderability						
	 (1) Use of Sn-63Pb solder Bath solder bath temperature = 230°C dipping time = 5 seconds the number of times = once use of R-type flux 					
	 (2) Use of Sn-3.0Ag-0.5Cu solder Bath solder bath temperature = 245°C dipping time = 5 seconds the number of times = once use of R-type flux 					

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 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as

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